## MT3401

# P-Channel Enhancement Mode Field Effect Transistor

## **Product Summary**

PRODUCT SUMMARY							
V <sub>DSS</sub>	ΙD	RDS(ON) $(m\Omega)$ Typ					
-30V	561	45@ VGS=-10V					
	-5.6A	65 @ VGS=-4.5V					

## **Features**

- Super high dense cell design for low RDS(ON)
- · Rugged and reliable
- Simple drive requirement

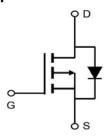
## **Applications**

· LED Display

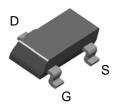


http://www.mtsemi.com

## **Simplified Schematic**



MARKING DIAGRAM & PIN ASSIGNMENT



SOT-23-3L

## **Absolute Maximum Ratings**(T<sub>A</sub> = 25°C unless otherwise noted)

Parameter Sym	bol	Limit	Unit
Drain-Source Voltage	$V_{\mathrm{DS}}$	-30	V
Gate-Source Voltage	Vgs	±20	V
Drain Current-Continuous <sup>a</sup> @Tj=25°C	ID	-5.6	A
- Pulse $d^b$	Ірм	-25	A
Drain-source Diode Forward Current <sup>a</sup>	Is	-1.5	A
Maximum Power Dissipation <sup>a</sup>	PD	1.5	W
Operating Junction and Storage Temperature Range	Тл,Тѕтб	-55 to 150	°C

## THERMAL CHARACTERISTICS

Thermal Resistance, Junction-to Ambient <sup>a</sup> Rth	JA	90	°C/W
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## ELECTRICAL CHARACTERISTICS (TA=25° unless otherwise noted)

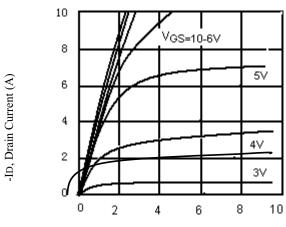
Parameter Sym	bol	Condition	Min	Тур	Max	Uni
OFF CHARACTERISTICS						I
Drain-Source Breakdown Voltage	BVDSS	V <sub>GS</sub> =0V,I <sub>D</sub> =-250µA		-30		V
Zero Gate Voltage Drain Current	IDSS	V <sub>DS</sub> =-30V,V <sub>GS</sub> =0V			1	μД
Gate-Body Leakage	Igss	Vgs=±10V,Vds=0V			±100	nA
ON CHARACTERITICS			_			
Gate Threshold Voltage	VGs(th) V	$_{DS}$ = $V_{GS}$ , $I_{D}$ =-250 $\mu A$	-1.2		-2.0	V
Durin Course On Chata Barintana	Dragon	Vgs=-10V,ID=-4.6A		45	50	0
Drain-Source On-State Resistance	RDS(ON)	V <sub>GS</sub> =-4.5V,I <sub>D</sub> =-3.0A		65	70	mΩ
Forward Transconductance	gFS	gfs V <sub>GS</sub> =-10V,I <sub>D</sub> =-1.7A				S
DAYNAMIC CHARACTERISTICS						•
Input Capacitance	Ciss			1226		pF
Output Capacitance	Coss	$V_{DS}=-15V, V_{GS}=0V$ f=1.0MHz		187		pF
Reverse Transfer Capacitance	Crss	1 1.011112		91		pF
SWITCHING CHARACTERISISTICS						
Turn-On Delay Time	tD(ON)	V <sub>DD</sub> =-15V		5.9		ns
Rise Time	tr	I <sub>D</sub> =-1.0A,		6.9		ns
Turn-Off Delay Time	tD(OFF)	V <sub>GEN</sub> =-10V R <sub>L</sub> =150hm		48		ns
Fall Time	tf	RGEN=60hm		16		ns
Total Gate Charge	Qg			9.8		nC
Gate-Source Charge	Qgs	VDS=-15V,ID=-1.7A		1.8		пC
Gate-Drain Charge	Qgd	Qgd VGS=-10V				nC

## ELECTRICAL CHARACTERICS (TA=25°C unless otherwise noted)

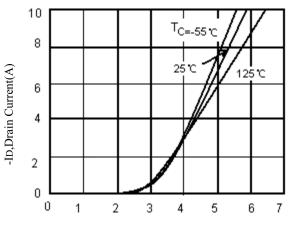
Parameter Sym	bol	Condition	Min	Тур	Max	Unit			
DRAIN-SOURCE DIODE CHARACTERISTICS									
Diode Forward Voltage	Vsd	Vgs=0V,Is=-1.25A		-0.8	-1.2	V			

#### Notes

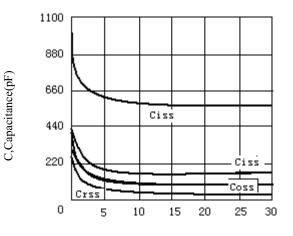
- a. Surface Mounted on FR4 Board, t≤10sec
- b. Pulse Test: Pulse Width ≤ 300Us, Duty Cycle ≤ 2%
- c. Guaranteed by design, not subject to production testing.



- VDS, Drain-to-Source Voltage (V) Figure 1.Output Characteristics



-Vcs, Gate-to-source Voltage (V) Figure 2. Transfer Characteristics



- VGS, Drain-to Source Voltage

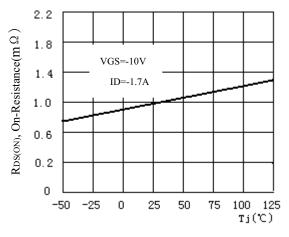
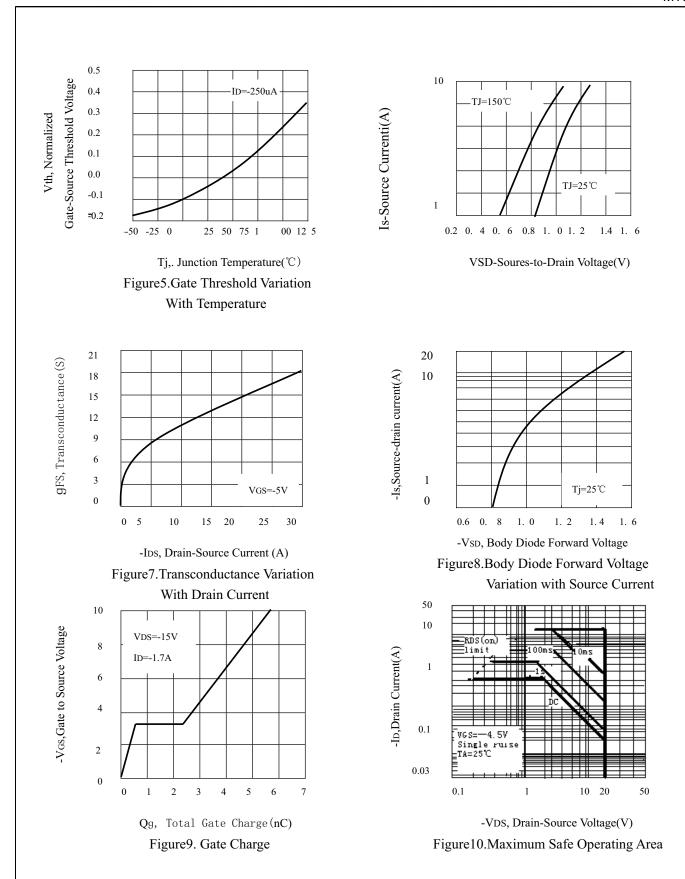


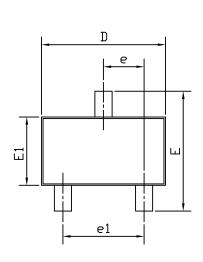
Figure 4. On-Resistance Variation with Temperature

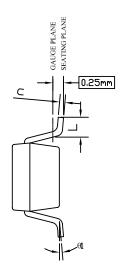
Figure 3. Capacitance

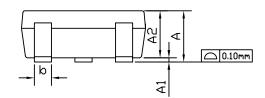


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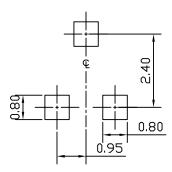
## SOT23 PACKAGE OUTLINE







#### RECOMMENDED LAND PATTERN

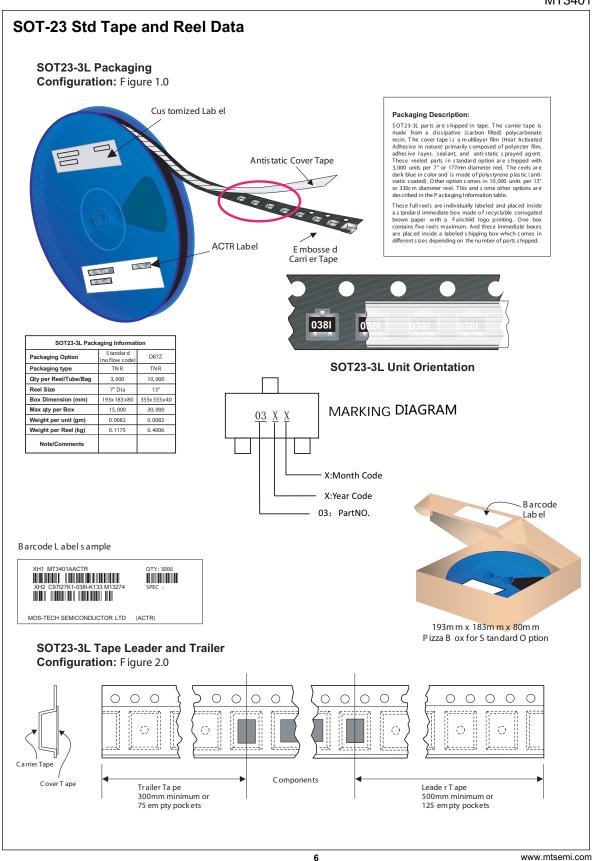


UNIT: mm

SYMBOLS	DIMENS	IONS IN MILLI	METERS	DIMENSIONS IN INCHES			
31 MBOL3	MIN	NOM	MAX	MIN	NOM	MAX	
A	0.85		1.25	0.033		0.049	
A1	0.00		0.13	0.000		0.005	
A2	0.70	1.00	1.15	0.028	0.039	0.045	
b	0.30	0.40	0.50	0.012	0.016	0.020	
С	0.08	0.13	0.20	0.003	0.005	0.008	
D	2.80	2.90	3.10	0.110	0.114	0.122	
Е	2.60	2.80	3.00	0.102	0.110	0.118	
E1	1.40	1.60	1.80	0.055	0.063	0.071	
e	0.95 BSC 0.037				0.037 BSC		
e1		1.90 BSC		0.075 BSC			
L	0.30		0.60	0.012		0.024	
θ1	0°	5°	8°	0°	5°	8°	

#### NOTE

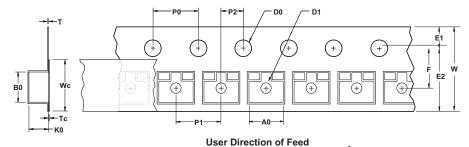
- 1. PACKAGE BODY SIZES EXCLUDE MOLD FLASH OR GATE BURRS. MOLD FLASH AT THE NON-LEAD SIDES SHOULD BE LESS THAN 5 MILS EACH.
- 2. TOLERANCE  $\pm 0.100$  mm (4 mil) UNLESS OTHERWISE SPECIFIED.
- 3. DIMENSION L IS MEASURED IN GAUGE PLANE.
- 4. CONTROLLING DIMENSION IS MILLIMETER. CONVERTED INCH DIMENSIONS ARE NOT NECESSARILY EXACT.
- 5. ALL DIMENSIONS ARE IN MILLIMETERS.



## SOT-23 Std Tape and Reel Data, continued

### **SOT23-3L Embossed Carrier Tape**

Configuration: Figure 3.0

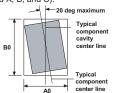


	Dimensions are in millimeter													
Pkg type	Α0	В0	w	D0	D1	E1	E2	F	P1	P0	K0	т	Wc	Тс
SOT-23 (8mm)	3.15 +/-0.10	2.77 +/-0.10	8.0 +/-0.3	1.55 +/-0.05	1.125 +/-0.125	1.75 +/-0.10	6.25 min	3.50 +/-0.05	4.0 +/-0.1	4.0 +/-0.1	1.30 +/-0.10	0.228 +/-0.013	5.2 +/-0.3	0.06 +/-0.02

Notes: A0, B0, and K0 dimensions are determined with respect to the EIA/Jedec RS-481 rotational and lateral movement requirements (see sketches A, B, and C).



Sketch A (Side or Front Sectional View)
Component Rotation



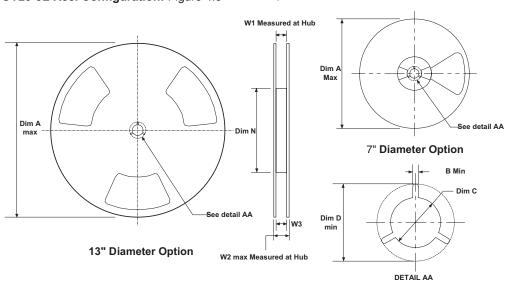
Sketch B (Top View)

Component Rotation



Sketch C (Top View)
Component lateral movement

## SOT23-3L Reel Configuration: Figure 4.0



	Dimensions are in inches and millimeters										
Tape Size Reel Option Dim A Dim B Dim C Dim D Dim N Dim W1 Dim W2 Dim W3 (LSI							Dim W3 (LSL-USL)				
8mm	7" Dia	7.00 177.8	0.059 1.5	512 +0.020/-0.008 13 +0.5/-0.2	0.795 20.2	2.165 55	0.331 +0.059/-0.000 8.4 +1.5/0	0.567 14.4	0.311 - 0.429 7.9 - 10.9		
8mm	13" Dia	13.00 330	0.059 1.5	512 +0.020/-0.008 13 +0.5/-0.2	0.795 20.2	4.00 100	0.331 +0.059/-0.000 8.4 +1.5/0	0.567 14.4	0.311 - 0.429 7.9 - 10.9		

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